Ref	Hits	Search Query	DBs	Default	Plurals	Time Stamp
121	283	(normal near3 test\$3) same (burn near5 test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	Operator OR	ON	2006/06/14 12:46
L2	64	L1 same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:46
L3	7	L2 same current\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:46
L4	190	(burn near5 test\$3) same (leak\$3 near3 current\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:46
L5	59	L4 and ((word adj2 line) or word\$1lin\$2 or "word line")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:46
L6	15	L5 and (stress\$2 adj3 voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:46
L7	50	(burn near5 test\$3) same (word adj5 line adj5 driver)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47
L8	7	L7 and PMOS\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47

L9	213	(burn near5 test\$3) and (word adj5 line adj5 driver)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47
L10	39	L9 and PMOS and (high adj3 voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47
L11	33	L10 and (low adj3 voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47
L12	23	L11 and pre\$1determined	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47
L13	22	(switch adj2 circuit) and (normal adj2 data) and (burn adj3 test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:48
L14	22	L13 and operation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:48
L15	22	L14 and (bit wit line with stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:48
L16	22	L15 and (voltag\$2 or power or potential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:30

L17	1	(memory and (burn near3 test) and array and (word near2 lines) and column and (leak near3 current) and pre\$1determin\$3 and (stress near3 voltage)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:32
L18	1	(method and (word near3 line near3 driver) and (burn near3 test) and cell and load and PMOS and source and gate and drain and pre\$1determin\$3 and voltage). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:34
L19	1	(switch and normal and data and (burn near2 test) and cell and (bit near2 line) and read and write and stress and voltage).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:35
L20	1	(memory and (burn near3 test) and array and (word near2 line) and (bit near2 line) and column and row and switch and normal and (word near3 line near3 driver) and PMOS).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:37
L23	6	chou-min-chung.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:38
L24	2	23 and 16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 13:38
S1	3368	365/201.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 14:46
S2	3746	365/230.06.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 14:46

S3	1692	365/230.08.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 14:46
S4	280	(normal near3 test\$3) same (burn near5 test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 14:52
S5	63	S4 same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 14:47
S6	7	S5 same current\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:46
S7	182	(burn near5 test\$3) same (leak\$3 near3 current\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:34
S8	16	S7 same ((word adj2 line) or word\$1lin\$2 or "word line")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 14:53
S9	57	S7 and ((word adj2 line) or word\$1lin\$2 or "word line")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 14:54
S10	12	S9 and (stress\$2 adj2 voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:46

S11	46	(burn near5 test\$3) same (word adj5 line adj5 driver)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:34
S12	6	S11 and PMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47
S13	205	(burn near5 test\$3) and (word adj5 line adj5 driver)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:35
S14	38	S13 and PMOS and (high adj3 voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:35
S15	32	S14 and (low adj3 voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:35
S16	22	S15 and predetermined	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:47
S17	1	(switch adj2 circuit) same (normal adj2 data) same (burn adj3 test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:36
S18	21	(switch adj2 circuit) and (normal adj2 data) and (burn adj3 test\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:37

S19	21	S18 and operation	US-PGPUB;	OR	ON	2006/02/18 15:37
			USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			
S20	1	S19 and (bit adj3 line adj3 stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:37
S21	21	S19 and (bit wit line with stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:37
S22	21	S21 and (voltage or power or potential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 12:48
S23	25	S9 and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:39
S24	7	S9 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:39
S25	0	S9 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/02/18 15:39
S26	7	S22 and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:39

S27	0	S22 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:39
S28	2	S22 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:39
S29	7	S22 and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:40
S30	1	S11 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:40
S31	1	(memory and (burn adj2 test) and array and (word adj2 line) and (leak\$3 with current\$2) with limit\$2 and (predetermin\$2 with word with line with current) and (stress with voltage) and column). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:44
S32	1	(method and (word with line with driver) and impedance and (burn with test\$3) and (PMOS with transistor) and source and drain and gate and (word with lin\$2) and predetermin\$3 and (high with voltage) and (low with voltage)).	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:46
S33	1	((switch with circuit) and (normal with data with path) and (burn with test with path) and (burn with test\$3 with row) and (data with unit) and (bit with line) and (normal with mode) and (read with write with operat\$3) and perform\$3 and (burn with test with mode) and (bit with line with stress with voltage)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 15:49

S34	1	(memory and (burn with test\$3) and (memory with circuit) and array and (word with line) and column and (bit with line) and select\$3 and (switch\$3 with circuit) and (normal with data with path) and (burn with test with path) and row and (word with line with driver\$2) and (PMOS with transistor) and source and gate and drain).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:03
S35	0	chou-min.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:03
S36	29	chou-min-\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:03
S37	5	chou-min-chung.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:03
S38	1	S36 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:03
S39	1	S36 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:03
S40	1	S36 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:04

S41	1	S36 and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:04
S42	1	S36 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:04
S43	1	S36 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/18 16:04

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